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cont

formed and an opening including the seal member layer 64A is formed in the second photosensitive material layer 62 and the opening is stretched in a horizontal direction.

Replace the paragraph beginning on page 29, line 21 with the following paragraph:

As shown in FIG. 24C, a sealing material layer 64B is filled in the opening 20.

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Likewise, as shown in FIG. 24D, a third photosensitive material layer 66 is formed, then an opening is defined. The opening is formed in a position extended in the vertical direction of the opening as shown in FIG. 24D. The sealing member layer 64C is filled in the opening.

Replace the paragraph beginning on page 33, line 11 with the following paragraph:

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As shown in FIG. 27C and FIG. 27D, an insulating layer 85 is formed on a first temporary board 84A by a CVD or sputtering technique. Although it is preferable that the first temporary board 84A is formed of a silicon semiconductor board, it may be formed of other boards such as quartz board and the like. A thickness of insulating layer 85 is preferable to range from 0.5 μm to 1.5 μm .

Replace the paragraph beginning on page 33, line 20 with the following paragraph: